L Number	Hits	Search Text	DB	Time stamp
-	1214	257/506	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/31 14:32
-	164	438/$.ccls. and trench and angle and (radio adj frequency)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/09 18:20
-	10	438/$.ccls. and trench and angle and (radio adj frequency) and polymer and (fluorocarbon adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 09:04
-	81	438/$.ccls. and CF and CHF	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 08:03
-	43	257/347 and ((gate adj electrode) WITH trench) and SOI	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 08:57
-	88	257/347 and ((gate adj electrode) same trench) and SOI	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 08:58
-	215	((tetrafluoromethane or "CF.sub.4") near2 (trifluoromethane or "CHF.sub.3")) same ratio same (plasma or etch or etch$3 or RIE) and 438/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/08 08:41
-	316	((tetrafluoromethane or "CF.sub.4") near2 (trifluoromethane or "CHF.sub.3")) same ratio same (plasma or etch or etch$3 or RIE)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/08 08:25
-	178	((tetrafluoromethane or "CF.sub.4") near2 (trifluoromethane or "CHF.sub.3")) same (trench) and 438/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/07 17:53
-	716	438/$.ccls. and (trench or (isolation adj trench)) and angle and (dielectric adj material)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/08 09:32
-	25	438/207 and trench and angle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/08 10:08
-	18	438/219 and trench and angle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/08 10:12
-	70	438/221 and trench and angle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/08 10:36
-	32	438/218 and trench and angle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/08 10:47

-	17	438/225 and trench and angle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/08 10:54
-	42	438/294 and trench and angle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/08 10:59
-	158	438/296 and trench and angle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/08 13:21
-	40	438/297 and trench and angle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/08 13:29
-	41	438/404 and trench and angle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/08 13:48
-	262	438/424 and trench and angle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/08 14:18
-	57	438/425 and trench and angle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/08 14:25
-	119	438/427 and trench and angle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/08 14:35
-	25	438/439 and trench and angle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/08 14:38
-	104	257/506 and trench and angle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/14 10:43
-	36	257/508 and trench and angle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/08 14:48
-	139	257/510 and trench and angle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/28 08:30
-	134	((side adj wall) with polymer) and trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/15 15:55
-	1592	(side adj wall) with polymer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/15 15:51

-	118	((side adj wall) with polymer) and trench and etching	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/15 15:56
-	12	((side adj wall) with polymer) with trench with etching	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/16 16:07
-	59	438/$.ccls. and (benefits with masking)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/16 16:10
-	483	etching with gas with (radio adj frequency)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 09:06
-	74	etching with ((tetrafluoromethane or "CF.sub.4") or (trifluoromethane or "CHF.sub.3")) with (radio adj frequency)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/05 16:44
-	53	257/314 and profile and floating and ONO	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/05 17:31
-	252	(flash adj memory) and amorphous and ONO and (trench$2 or STI$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/05 17:34
-	66	257/$.ccls. and trench and (dielectric with (etching near (over-etching)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 08:06
-	209	257/$.ccls. and (mask$4 with (over-etching))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/10 18:51
-	235	257/$.ccls. and trench and angle and (over adj etching)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 14:15
-	23	(semiconductor adj substrate) and de-chuck$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:00
-	15	(semiconductor adj substrate) and de-chuck$ and argon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:10
-	36	etching and de-chuck$ and argon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 13:52
-	39	438/$.ccls. and (etch with ((over-etching) or (over adj etching)) with plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 15:37

-	32	438/294 and (plasma and gases and trench and ((nitride adj layer) and (oxide adj layer)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 15:20
-	110	438/$.ccls. and (etch and ((over-etching) or (over adj etching)) with plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 14:56
-	18	((masking adj layer) and (microwave same plasma) and (magnetron))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 17:00
-	12	257/$.ccls. and ((masking adj layer) and (microwave same plasma) and (magnetron))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 15:43
-	15	438/$.ccls. and ((masking adj layer) and (microwave same plasma) and (magnetron))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 15:48
-	18	etching and (masking adj layer) and (microwave same plasma) and (magnetron)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/11 14:26
-	750	438/207	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/14 10:50
-	393	438/218	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/14 10:54
-	159	438/219	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/14 10:57
-	546	438/294	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/14 11:03
-	1262	438/296	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/14 11:17
-	324	438/353	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/14 11:21
-	173	438/361	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/14 11:23
-	203	438/362	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/14 11:26

-	548	438/221		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/14 11:33
-	1539	257/506		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/14 11:48
-	229	257/507		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/14 11:50
-	618	257/508		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/14 11:56
-	298	257/509		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/14 12:00
-	1128	257/510		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/14 12:01